1N253

SILICON POWER RECTIFIER

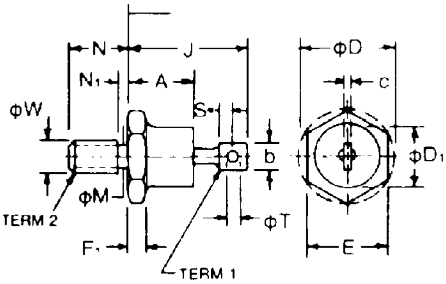
DESCRIPTION:

The **ASI 1N253** is Designed for General Purpose Power Supply Applications.

MAXIMUM RATINGS

I_o	1.0 A @ T_C = 135 °C
V_{RWM}	100 V
T_J	-65 °C to +170 °C
T_{STG}	-65 °C to +175 °C
θ_{JC}	35 °C/W

PACKAGE STYLE DO- 4



Cathode to Stud

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A		0.405		10.28
b		0.250		6.35
c				
ΦD		0.505		12.82
ΦD₁	0.265	0.424	6.74	10.76
E	0.423	0.438	10.75	11.12
F₁	0.075	0.175	1.91	4.44
J	0.600	0.800	15.24	20.32
ΦM	0.163	0.189	4.15	4.80
N	0.422	0.453	10.72	11.50
N₁		0.078		1.98
S				
ΦT	0.060	0.095	1.53	2.41
ΦW	10-32	UNF-2A	10-32	UNF-2A

CHARACTERISTICS T_J = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIM	UNITS
I_R	V_R = 100 V T_J = 150 °C		10 100	100 1000	µA
V_F	I_F = 1.0 A			1.2	V
I_{FSM}	NON REPETITIVE t_p = 8.3 mS	15			A